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FAIRCHILD

NPN General Purpose Amplifier

This device is for use as a medium power amplifier and switch requiring collector currents up to 500 mA. Sourced from Process 19. See PN2222A for characteristics.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	40	V
V _{CBO}	Collector-Base Voltage	75	V
V _{EBO}	Emitter-Base Voltage	6.0	V
I _C	Collector Current - Continuous	1.0	А
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Мах	Units
		TN2219A	
PD	Total Device Dissipation	1.0	W
	Derate above 25°C	8.0	W/°C
R _{0JC}	Thermal Resistance, Junction to Case	125	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	50	°C/W

NPN General Purpose Amplifier (continued)

TN2219A

$\begin{tabular}{ c c c c c c c c c c c c c c c c c c c$	Symbol	Parameter	Test Conditions	Min	Max	Units
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $		DAGTERIOTIOO				
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $						
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	V _{(BR)CEO}	Collector-Emitter Breakdown Voltage*	$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 0$	40		V
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_{\rm C} = 10 \ \mu {\rm A}, \ I_{\rm E} = 0$	75		V
OLX Collector Cutoff Current $V_{CB} = 60 \text{ V}, I_E = 0$ 10 I_{CBO} Collector Cutoff Current $V_{CB} = 60 \text{ V}, I_E = 0, T_A = 150^{\circ}\text{C}$ 10 I_{EBO} Emitter Cutoff Current $V_{EB} = 3.0 \text{ V}, I_C = 0$ 10 I_{BL} Base Cutoff Current $V_{CE} = 60 \text{ V}, V_{EB(OFF)} = 3.0$ 20 ON CHARACTERISTICS h_{FE} DC Current Gain $I_C = 0.1 \text{ mA}, V_{CE} = 10 \text{ V}$ 35 $I_C = 10 \text{ mA}, V_{CE} = 10 \text{ V}$ 50 10 300 $I_C = 150 \text{ mA}, V_{CE} = 10 \text{ V}$ 75 100 300 $I_C = 150 \text{ mA}, V_{CE} = 10 \text{ V}$ 100 300 10 $V_{CE(sat)}$ Collector-Emitter Saturation Voltage* $I_C = 150 \text{ mA}, I_B = 15 \text{ mA}$ 0.3 $V_{EE(sat)}$ Base-Emitter Saturation Voltage* $I_C = 150 \text{ mA}, I_B = 1.0 \text{ mA}$ 0.6 1.2		Emitter-Base Breakdown Voltage	$I_{\rm E} = 10 \ \mu {\rm A}, \ I_{\rm C} = 0$	6.0		V
V _{GB} 60 V, I _E 0, T _A 150°C 10 I _{EBO} Emitter Cutoff Current V _{EB} 3.0 V, I _C 0 10 I _{BL} Base Cutoff Current V _{CE} 60 V, V _{EB} 3.0 20 ON CHARACTERISTICS h _{FE} DC Current Gain I _C 1 1 35 1 I _C 1.0 mA, V _{CE} 10 V 50 1 50 1 V _{CE} (sat) Collector-Emitter Saturation Voltage* I _C 150 mA, I _B 10 V 50 V _{CE(sat)} Base-Emitter Saturation Voltage* I _C 150 mA, I _B 0.6 1.2	I _{CEX}	Collector Cutoff Current	$V_{CE} = 60 \text{ V}, V_{EB(OFF)} = 3.0 \text{ V}$		10	nA
V _{CB} = 60 V, I _E = 0, T _A = 150°C 10 I _{EBO} Emitter Cutoff Current V _{EB} = 3.0 V, I _C = 0 10 I _{BL} Base Cutoff Current V _{CE} = 60 V, V _{EB(OFF)} = 3.0 20 ON CHARACTERISTICS IC = 0.1 mA, V _{CE} = 10 V 35 20 ON CHARACTERISTICS IC = 1.0 mA, V _{CE} = 10 V 35 30 V _{EE} = 10 V 10 V 35 10 100 V _{CE} = 10 V 50 10 300 10 V _{CE} = 10 V 75 100 300 300 V _{CE} (sat) Collector-Emitter Saturation Voltage* IC = 150 mA, I _B = 15 mA 0.3 0.3 V _{BE(sat)} Base-Emitter Saturation Voltage* IC = 150 mA, I _B = 1.0 mA 0.6 1.2	I _{CBO}	Collector Cutoff Current	$V_{CB} = 60 \text{ V}, I_E = 0$		10	nA
			$V_{CB} = 60 \text{ V}, I_E = 0, T_A = 150^{\circ}\text{C}$		10	μA
	I _{EBO}	Emitter Cutoff Current	$V_{EB} = 3.0 \text{ V}, \text{ I}_{C} = 0$		10	nA
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	I _{BL}	Base Cutoff Current	$V_{CE} = 60 \text{ V}, V_{EB(OFF)} = 3.0$		20	nA
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$				05		
$\begin{tabular}{ c c c c c c c c c c c c c c c c c c c$	n _{FE}	DC Current Gain				
$\begin{tabular}{ c c c c c c c c c c c c c c c c c c c$						
$\begin{tabular}{ c c c c c c c c c c c c c c c c c c c$					300	
				50		
$I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$ 1.0 $V_{BE(sat)}$ Base-Emitter Saturation Voltage* $I_C = 150 \text{ mA}, I_B = 1.0 \text{ mA}$ 0.6 1.2			$I_{\rm C} = 500 \text{ mA}, V_{\rm CE} = 10 \text{ V}$	40		
$V_{BE(sat)}$ Base-Emitter Saturation Voltage* $I_{C} = 150 \text{ mA}, I_{B} = 1.0 \text{ mA}$ 0.6 1.2	V _{CE(sat)}	Collector-Emitter Saturation Voltage*	с , <u>с</u>			V
						V
I 500m/ 50m/ 50m/	V _{BE(sat)}	Base-Emitter Saturation Voltage*	$I_{\rm C} = 150 \text{ mA}, I_{\rm B} = 1.0 \text{ mA}$ $I_{\rm C} = 500 \text{ mA}, I_{\rm B} = 5.0 \text{ mA}$	0.6	1.2 2.0	V V

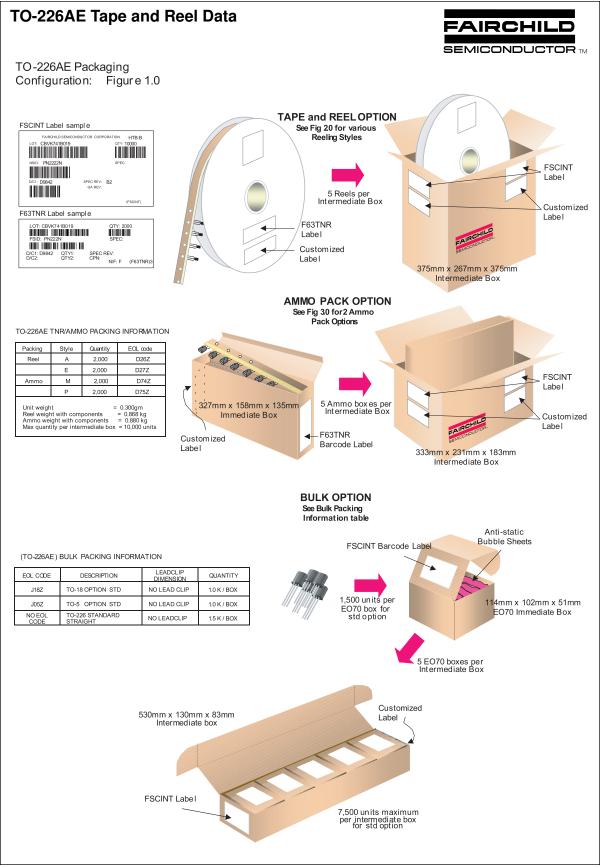
SMALL SIGNAL CHARACTERISTICS

Cobo	Output Capacitance	$V_{CB} = 10 \text{ V}, I_E = 0, f = 100 \text{ kHz}$		8.0	pF
Cibo	Input Capacitance	$V_{EB} = 0.5 \text{ V}, I_C = 0, f = 100 \text{ kHz}$		25	pF
h _{fe}	Small-Signal Current Gain	$I_{C} = 1.0 \text{ mA}, V_{CE} = 10 \text{ V}, f = 1.0 \text{ kHz}$ $I_{C} = 10 \text{ mA}, V_{CE} = 10 \text{ V}, f = 1.0 \text{ kHz}$	50 75	300 375	
rb'C _C	Collector Base Time Constant	$I_E = 20 \text{ mA}, V_{CB} = 20 \text{ V}, \text{ f} = 31.8 \text{ MHz}$		150	pS
NF	Noise Figure	$\label{eq:lc} \begin{array}{l} I_{C} = 100 \; \mu \text{A}, V_{CE} = 10 \; \text{V}, R_{S} = 1.0 \; \text{k}\Omega \\ f = 1.0 \; \text{kHz}, B_{W} = 1.0 \; \text{kHz} \end{array}$		4.0	dB
Re(h _{ie})	Real Part of Common-Emitter High Frequency Input Impedance	$I_{C} = 20 \text{ mA}, V_{CE} = 20 \text{ V}, f = 300 \text{ MHz}$		60	Ω

SWITCHING CHARACTERISTICS

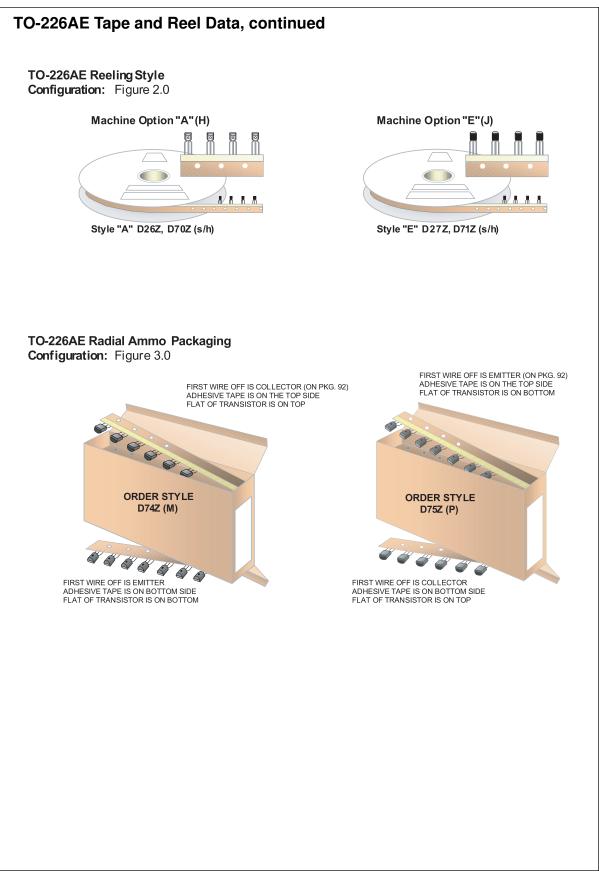
t _d	Delay Time	$V_{CC} = 30 \text{ V}, \text{ V}_{BE(OFF)} = 0.5 \text{ V},$	10	ns
t _r	Rise Time	$I_{\rm C} = 150 \text{ mA}, I_{\rm B1} = 15 \text{ mA}$	25	ns
ts	Storage Time	$V_{CC} = 30 \text{ V}, I_{C} = 150 \text{ mA},$	225	ns
t _f	Fall Time	$I_{B1} = I_{B2} = 15 \text{ mA}$	60	ns

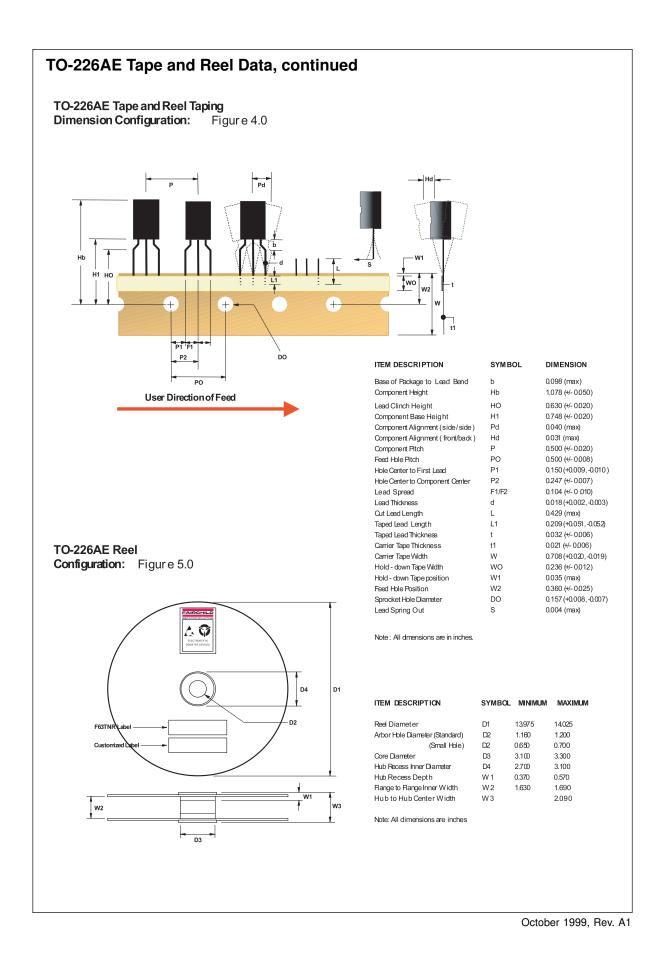
*Pulse Test: Pulse Width \leq 300 $\mu s,$ Duty Cycle \leq 2.0%

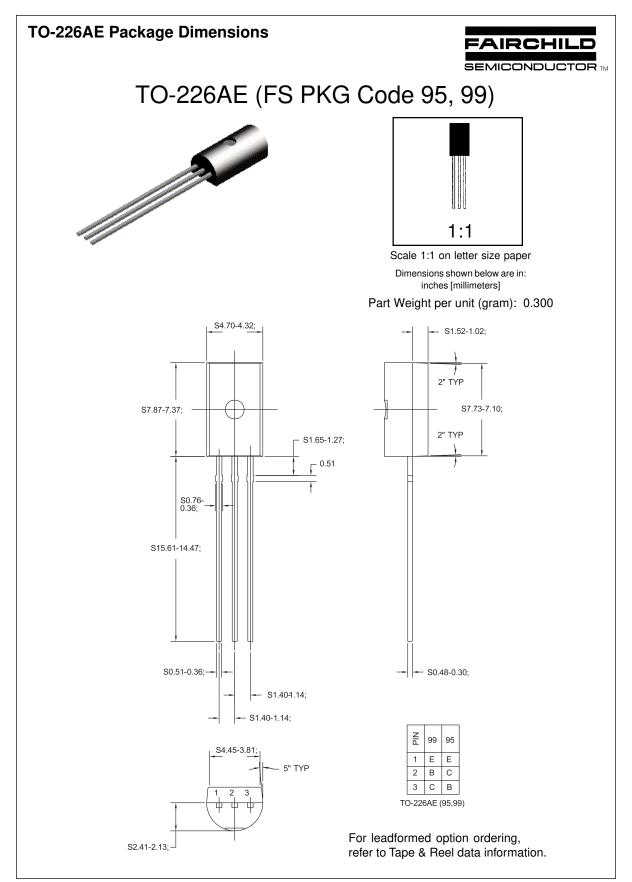


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